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## NPN EPITAXIAL SILICON TRANSISTOR

T-29-19

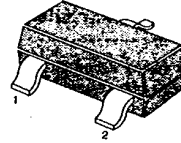
## AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	55	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	200	mA
Collector Dissipation	$P_C$	350	mW
Storage Temperature	$T_{stg}$	150	$^\circ\text{C}$

• Refer to MMBT5088 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = 0.1\text{mA}, I_E = 0$	55		V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = 1.0\text{mA}, I_B = 0$	45		V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 30\text{V}, I_E = 0$		0.01	$\mu\text{A}$
Collector Cutoff Current	$I_{CEO}$	$V_{CE} = 30\text{V}, I_B = 0$		0.1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5.0\text{V}, I_C = 0$		0.01	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 5\text{V}, I_C = 0.01\text{mA}$	500		
		$V_{CE} = 5\text{V}, I_C = 0.1\text{mA}$	500	1250	
		$V_{CE} = 5\text{V}, I_C = 1.0\text{mA}$	500		
		$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	500		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5\text{mA}$		0.2 0.6	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$	0.56	0.66	V
Current Gain-Bandwidth Product	$f_T$	$I_C = 1.0\text{mA}, V_{CE} = 5\text{V}$ $f = 100\text{MHz}$	100	700	MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0$ $f = 1.0\text{MHz}$		3	pF

Marking

